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- I. a) 1: Ch. Kleint:
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- 2: Ch. Kleint, R. Męclewski, R. Błaszczyszyn:
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- 3: M. Veselý:
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- 4: K. S. Bobev, G. D. Georgiev:
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- 5: K. S. Bobev, G. D. Georgiev:
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- 7: W. Schütt, H. Köster, G. Zuther:
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- 8: R. Hrach, Z. Hubička:
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- 9: H. Biederman:
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- 10: I. Emmer:
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- 11: H. Jahrreiss, W. Oppel:
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- 15: D. Fintelmann, W. Töpel:
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- 3: G. A. Nagy:
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- 6: M. Setvák:
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- I. c) 1: R. Harman, J. Liday, M. Veselý:
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- 2: B. Vlachová:
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- 10: G. Vágó, P. Glaser, A. Herman:
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- 3: L. Eckertová, J. Boček:
The mean free path of low energy electrons in thin Au films
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- 5: S. Koc, J. Zemek, M. Závětová:
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- 6: J. Zemek, S. Koc:
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- 8: I. Smetáková, M. Vaněček, R. Kužel:
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14: J. Sitek, K. Voleník:

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15: J. Walachová:

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16: R. Autrata, O. Vaněk:

DC - electroluminescence in thin films of ZnS

II. c) 1: V. I. Pokalyakin, G. V. Stepanov:

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2: Academy of Sciences, Moscow:

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- 3: O. Csabay:
Influence of surface treatment of silicon on the effective impurity charge density in surface states of MOS structures
- 4: M. Pawłowska, E. Sadłowska:
Semiconductor elements junction and surface layers examination
- 5: I. Adamčík, J. Schröfel:
Control of semiconductor-insulator interface characteristics in the MIS system
- 6: J. Jerhot, V. Šnejdar, D. Berková:
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- 7: I. Hüttel:
The analog scanning system of flat-screen displays
- 8: V. Dúbravcová, M. Jergel:
Micromachining of superconducting Nb₃Sn thin films by electron-beam microetching
- 9: E. Sumbalová, Š. Luby, V. Szobi:
Triming of tantalum thin film resistors through anodic oxidation with solid anodization probe
- 10: J. Badal:
Effects of substrate corrosion on thin films
- 11: V. Heřmanský:
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3: V. G. Kanev, K. S. Bobev, Z. D. Mireva:

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PAPERS RECEIVED AFTER DEAD-LINE

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- I. a) 21: A. N. Arsenjeva - Geil, N. G. Chernikov:
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- II. b) 17: F. Lukeš, K. Navrátil, I. Ohlídal, I. Sommer,
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